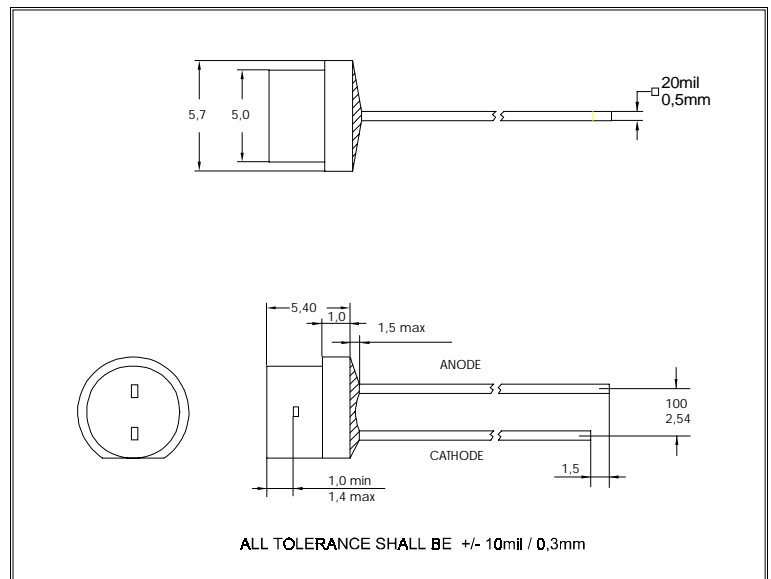


Infrared Light Emitting Diode IRED

870nm/20ns FQR5580

Features

- * Standard design LED for general purpose
Based on double hetero structure of GaAIAs
- * Low current and low degradation applications
- * Edged Corner Contact ; free top surface
- * Water-clear package style without stand-off
- * Application : Open-Air communication / IrDa
Lensed Optical Systems
Medical instruments
Encoder
Optical Measurement Systems



Electrical and optical characteristics and absolute maximum ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	MIN	Typ	MAX	Unit	Test conditions
I _F	DC Forward current			100	mA	
I _{PEAK}	Peak Forward current			1500	mA	Tp < 10µsec. ; T=1:1 Rtherm < 100 K/W
V _F	Forward Voltage	1,3	1,5	2,1	V	IF = 50mA
V _R	Reverse Voltage	5			V	Irev = 100µA
λ _{Peak}	Peak Wavelength	860	870	885	nm	IF = 50mA
Δλ _{0,5}	Bandwidth of half power	25	30		nm	IF = 50mA
t _f	Fall time		25		ns	IF = 100mA
t _r	Rise time		25		ns	IF = 100mA
F _E	Total Power Output	32	38		mW	IF = 100mA
I _E	Radiant Intensity		36		mW/sr	IF = 100mA
D	Diameter of light emitting point		TDB		mm	IF = 20mA, 63% of radiant output (IEC825)
A	Chip size		0,13		mm ²	Chip size : 360µmX360µm
d _c	Diameter of free emitting array		140		µm	from chip up to contact ring =70µm
2Φ _{0,5}	Emission Angle		110		deg.	FE = 50%
TK _{VF}	Temp.Coeff. of Forward Voltage		- 2		mV/K	
TK _F	Temp.Coeff. of Radiant Power		- 0,4		%/K	
T _{Operating}	Operating Temperature	- 25		85	°C	
T _{Storage}	Storage Temperature	- 25		85	°C	
T _{Soldering}	Soldering Temperature			260	°C	2mm from case @5 sec.
Θ _{j-PIN}	Thermal Resistance		450		K/W	
P _{tot}	Total Power Dissipation			230	mW	derate above 45°C 2,5mW/K

Order Informations :

FQR5580 Bulk
FQR5580TR Taped on Reel / 1000 pcs. standard reel
FQR5580TA Taped in AMMOPACK /2000 pcs.

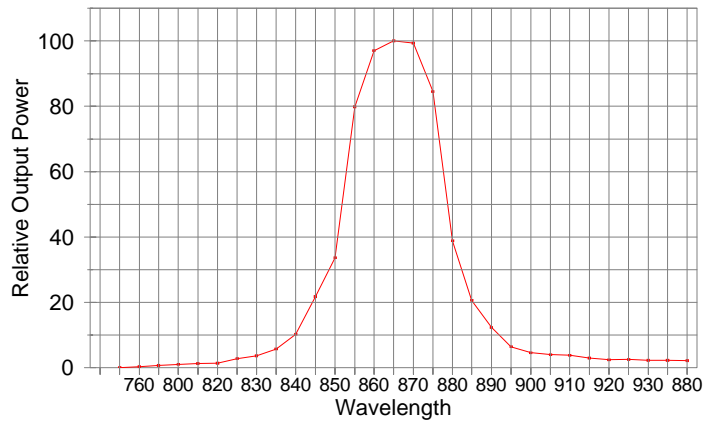
Fietje reserves the right to make changes at any time in order to improve design and to supply the best product possible, contact Fietje for latest device specification sheets before using.

Infrared Light Emitting Diode IRED

870nm/20ns

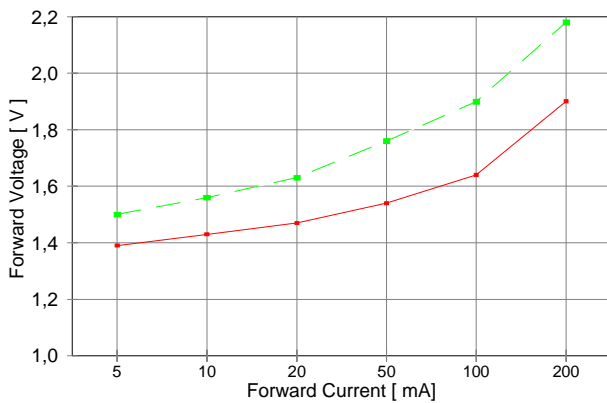
FQR5580

Relativ Spectral Emission

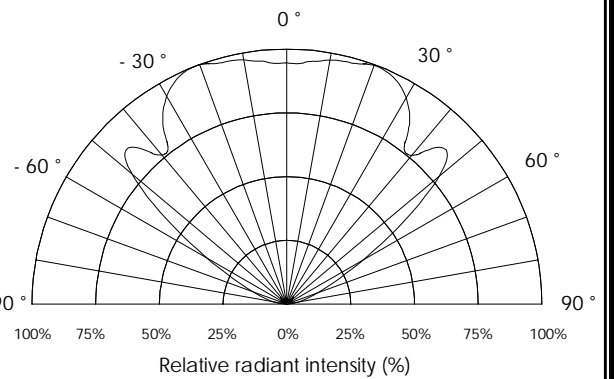


Forward Voltage

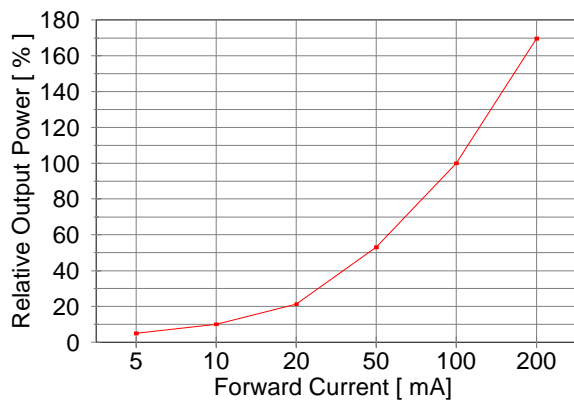
$V_f = f(I_f)$ typ.



Angular Displacement [degree]



Relative Output Power (typ.)



Relative Radiant Output Power (typ.)

